



SANYO SEMICONDUCTOR

2SD386, 386A
2SD387, 387A

(2SD386, 386A) — NPN Triple Diffused Planar Type Silicon Transistor
(2SD387, 387A) — For Vertical Deflection Output of Television

Absolute Maximum Ratings at Ta=25°C

	2SD386	2SD386A	2SD387	2SD387A	
Collector to Base Voltage, V_{CBO}	200	200	200	200	V
Collector to Emitter Voltage, V_{CEO}	120	150	120	150	V
Emitter to Base Voltage, V_{EBO}	6	6	6	6	V
Collector Current, I_C	3	2	3	2	A
Peak Collector Current, i_{CP}	10	10	10	10	A
Collector Dissipation, P_C	25	25	25	25	W
	$T_c=25^\circ\text{C}$	$T_c=25^\circ\text{C}$	$T_c=25^\circ\text{C}$	$T_c=25^\circ\text{C}$	W
Junction Temperature, T_j	150	150	150	150	°C
Storage Temperature, T_{stg}	→	→	→	-40→+150	°C

Electrical Characteristics at Ta=25°C

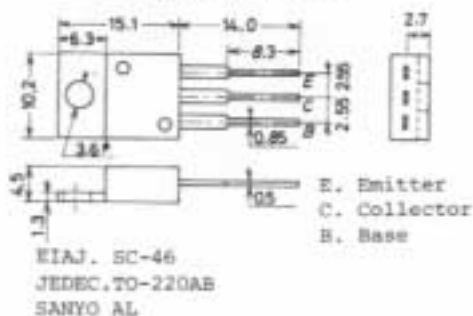
		min	typ	max	unit
Collector Cutoff Current, I_{CBO}	$V_{CB}=180\text{V}, I_E=0$			1.0	mA
Emitter Cutoff Current, I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			5	mA
DC Current Gain, h_{FE}^*	$V_{CE}=2\text{V}, I_C=0.5\text{A}$	40*		320*	
Gain Bandwidth Product, f_T	$V_{CE}=5\text{V}, I_C=0.5\text{A}$		8		MHz
C-E Saturation Voltage, $V_{CE(sat)}$	$I_C=1\text{A}, I_B=0.1\text{A}$	2SD386, 387		1.0	V
		2SD386A, 387A		1.5	V
B-E Saturation Voltage, $V_{BE(sat)}$	$I_C=1\text{A}, I_B=0.1\text{A}$			1.8	V

*2SD386, 386A, 387, 387A are classified as follows:

C:	40	80
D:	60	120
E:	100	200
F:	160	320

Case Outline (unit:mm)

2SD386, 386A



2SD387, 387A

